

The RM3002 is an NPN silicon planar photo sensitive Darlington Compound Amplifier. This device combines a lens window with an integral light sensing amplifier. The result is extreme sensitivity in a very small package. The planar construction and the stringent process controls prevalent at Raytheon insures the ultimate in reliability.

MECHANICAL DATA

CASE:

JEDEC TO-18

CONNECTION DIAGRAM:

TERMINAL CONNECTIONS:

Lead | Emitter

Lead 2 Base

Lead 3 Collector (Electrically connected to case)

20

ELECTRICAL DATA

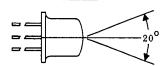
MAXIMUM RATINGS:

Collector to Base Voltage V _{CBO}	lts
Collector to Emitter Voltage (R _{BE} ≤10Ω) V _{CER}	
Collector to Emitter Voltage V _{CEO}	
Emitter to Base Voltage V _{EBO}	lts
Total Device Dissipation @ Case Temperature 25° C	itts itt itt

ELECTRICAL CHARACTERISTICS: @25°C (unless otherwise noted)

PARAMETER	SYM.	CONDITIONS	MIN.	MAX.	UNITS
Dark Current	ICEO	$V_{CE}^{=20} V$		10	mμA
Dark Current	ICEO	V _{CE} =20 V T=150° C		100	μΑ
Collector Dark Current	I _{CBO}	V _{CB} =30 V		10	$m \mu A$
Collector Dark Current	I _{CBO}	V _{CB} =30 V T=150° C		15	μΑ
Light Current Sensitivity		V _{CE} =12 100 foot candle illumination level	25 .	μ A/ft.	Candle

ALIGNMENT:



Maximum sensitivity falls within a 20° cone whose axis coincides with the central axis of the lens.

This document in part of the interested file. It separated from the US IS much be subjected to individual operatorial review.

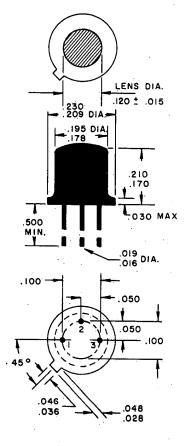
CALIFORNIA

PHOTO SENSITIVE DARLINGTON COMPOUNI AMPLIFIER

NPN PLANAR

FEATURES

- High Sensitivity
- 3 Lead Configuration
- High Stability
- Low Noise
- High Gain



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RAYTHEON COMPANY

SEMICONDUCTOR DIVISION

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